

**1. Amendments to the Specification**

Kindly replace the paragraph beginning on page 7, line 6 with the following amended paragraph:

A thin gold layer of 0.5 to 3 nm is present on a silicon semiconductor substrate with an oxidized surface. This semiconductor substrate is placed in a quartz tube at a first end of a furnace. A fixed target of InP is placed at a second end of the furnace such that ablated InP can be carried along by the gas flow to the substrate. The furnace is evacuated to below 10 Pa. Then the pressure is set for 3.10.sup.4 Pa with an Ar flow of 100 to 300 sccm. The furnace is heated to 500.degree. C. This breaks open the gold layer and forms clusters on a nanometer scale. At this temperature, the target is ablated with an ArF laser having a wavelength of 193 nm. This leads to a growth of nanowires 10 of InP with the Au clusters acting as ~~eatalysists~~catalysts. The nanowires obtained comprise a first region 1, a second region 2, and a third region 3.